SamHop Microelectronics Corp.

STM121N

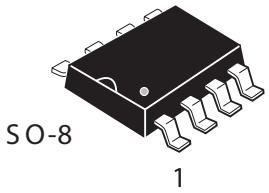
Ver 1.1

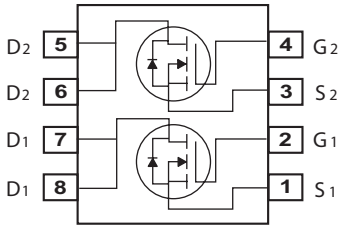
Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
100V	2.8A	155 @ VGS=10V
		192 @ VGS=4.5V

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- Suface Mount Package.





ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		100	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Drain Current-Continuous [a]	T_A=25°C	2.8	A
		T_A=70°C	2.2	A
I_{DM}	-Pulsed [b]		10	A
E_{AS}	Single Pulse Avalanche Energy [d]		12	mJ
P_D	Maximum Power Dissipation [a]	T_A=25°C	2	W
		T_A=70°C	1.28	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient [a]	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V , V_{GS}=0V			1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V , V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=250uA	1	1.9	3	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V , I_D=1.4A		124	155	m ohm
		V_{GS}=4.5V , I_D=1.25A		142	192	m ohm
g_{FS}	Forward Transconductance	V_{DS}=10V , I_D=1.4A		5		S
DYNAMIC CHARACTERISTICS [c]						
C_{ISS}	Input Capacitance	V_{DS}=25V,V_{GS}=0V f=1.0MHz		725	1015	pF
C_{OSS}	Output Capacitance			50	70	pF
C_{RSS}	Reverse Transfer Capacitance			32	60	pF
SWITCHING CHARACTERISTICS [c]						
$t_{D(ON)}$	Turn-On Delay Time	V_{DD}=50V I_D=1A V_{GS}=10V R_{GEN}= 6 ohm		11	22	ns
tr	Rise Time			10.7	20	ns
$t_{D(OFF)}$	Turn-Off Delay Time			21.5	43	ns
tf	Fall Time			11	22	ns
Q_g	Total Gate Charge	V_{DS}=50V,I_D=1.4A,V_{GS}=10V		10	14	nC
Q_{gs}	Gate-Source Charge	V_{DS}=50V,I_D=1.4A, V_{GS}=10V		1.4	2	nC
Q_{gd}	Gate-Drain Charge			2.6	3.6	nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=1A		0.78	1.3	V

Notes

a.Surface Mounted on FR4 Board,t ≤ 10sec.
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
c.Guaranteed by design, not subject to production testing.
d.Starting T_J=25°C,L=0.5mH,V_{DD} = 50V.(See Figure13)

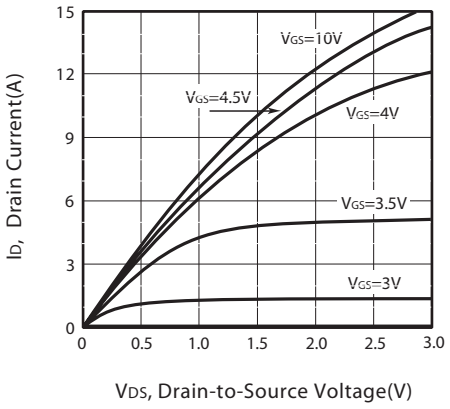


Figure 1. Output Characteristics

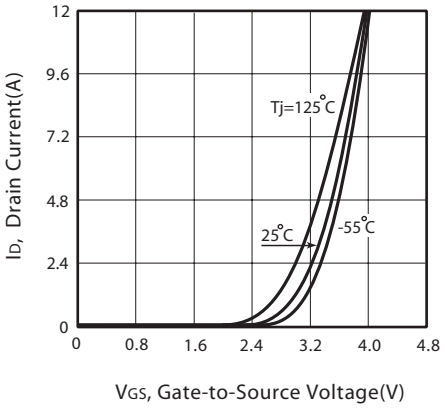


Figure 2. Transfer Characteristics

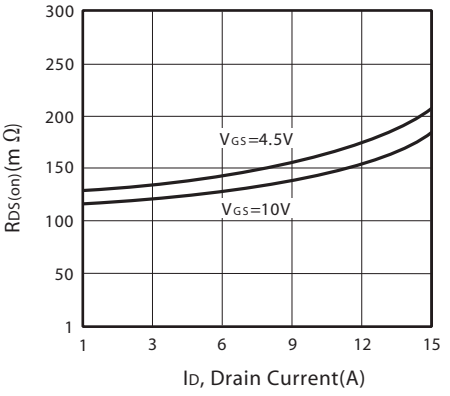


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

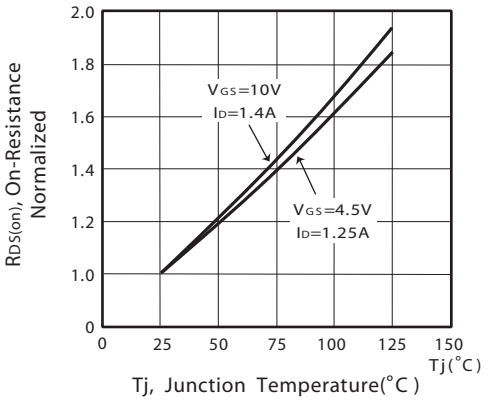


Figure 4. On-Resistance Variation with Drain Current and Temperature

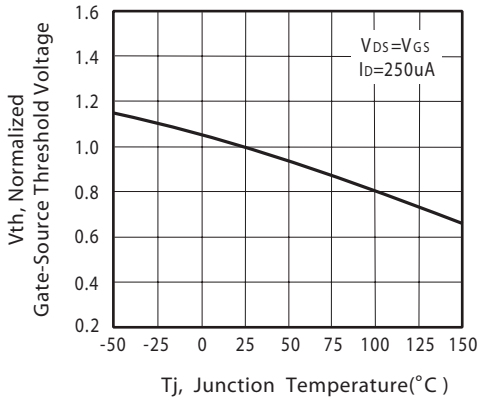


Figure 5. Gate Threshold Variation with Temperature

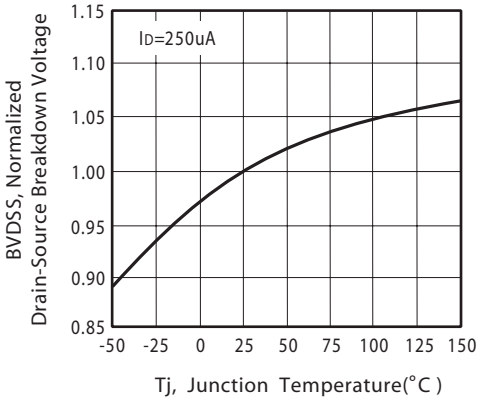


Figure 6. Breakdown Voltage Variation with Temperature

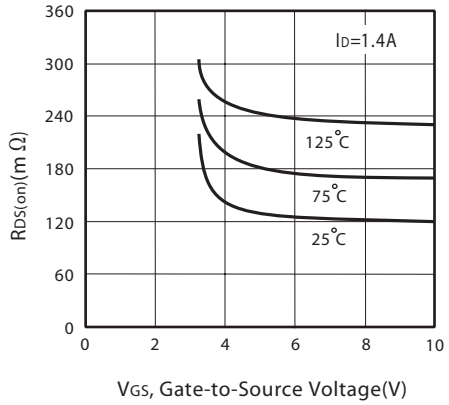


Figure 7. On-Resistance vs. Gate-Source Voltage

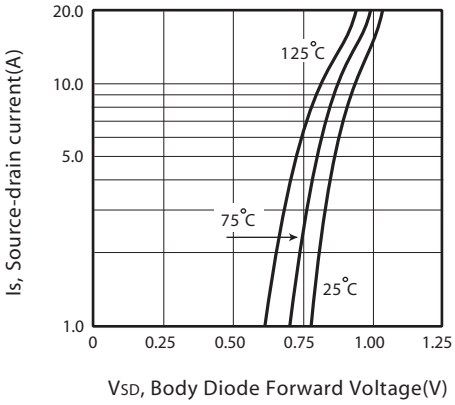


Figure 8. Body Diode Forward Voltage Variation with Source Current

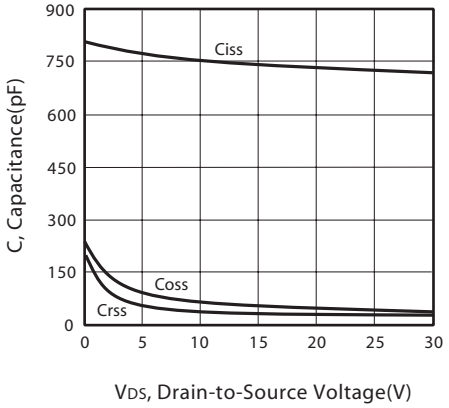


Figure 9. Capacitance

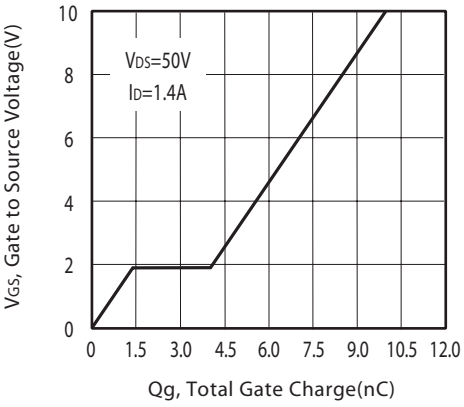


Figure 10. Gate Charge

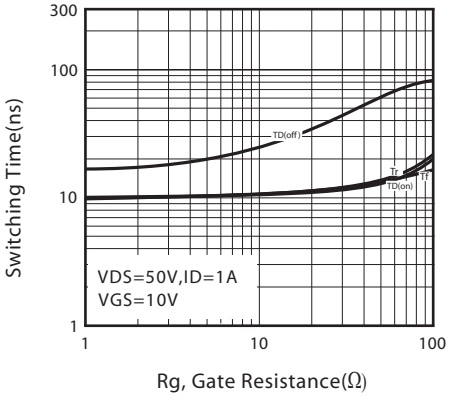


Figure 11. switching characteristics

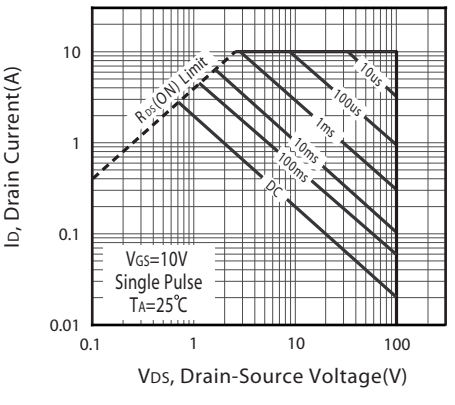
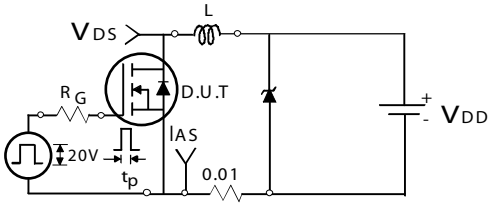
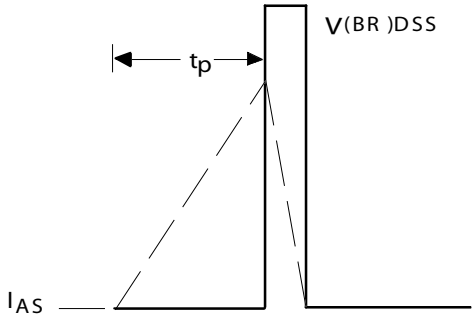


Figure 12. Maximum Safe Operating Area



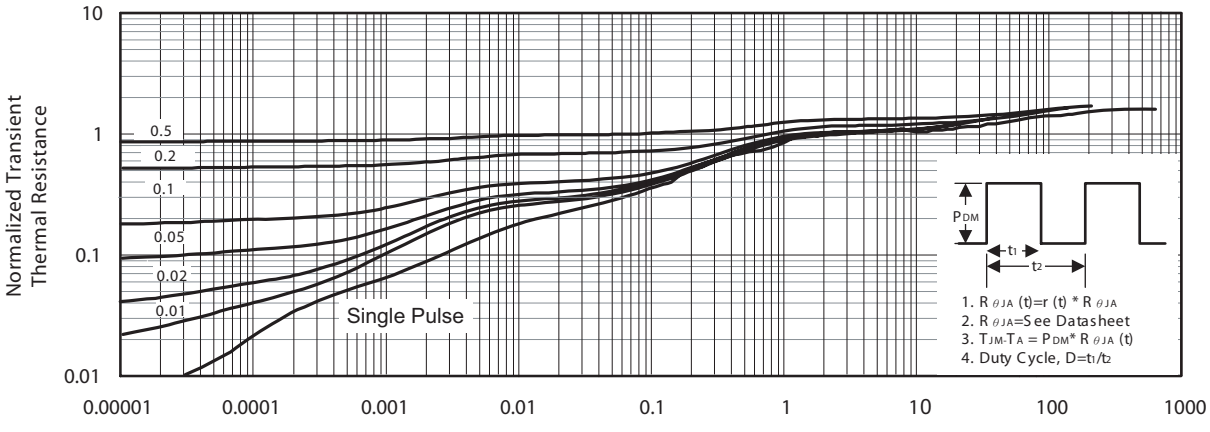
Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

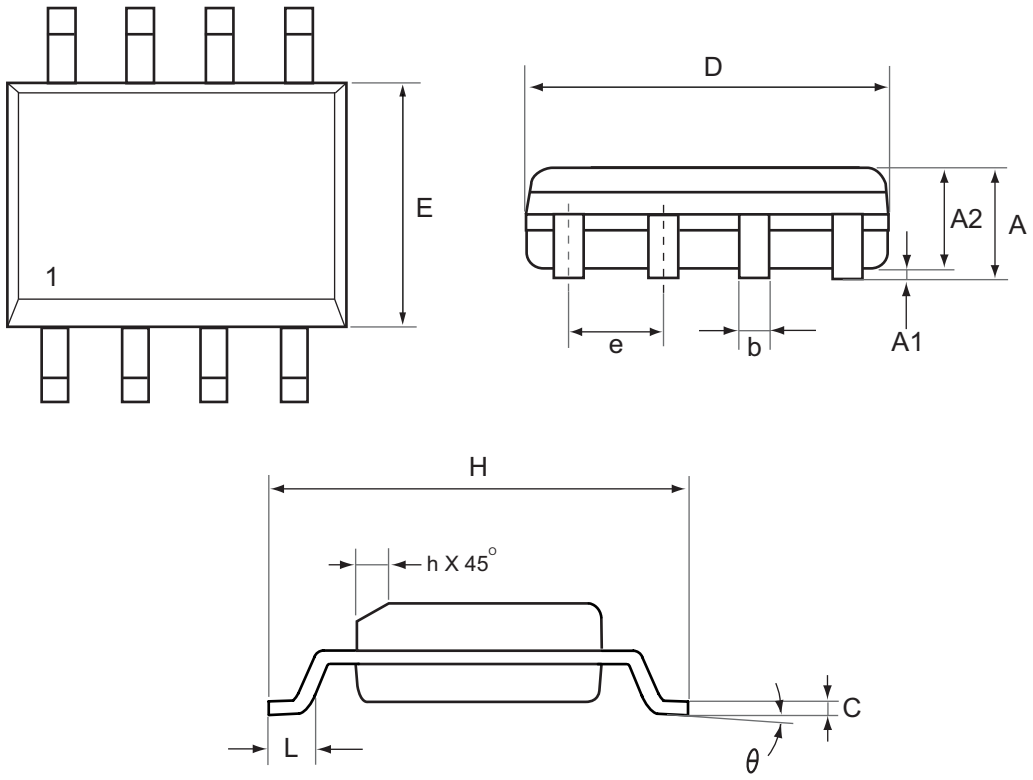
Figure 13b.



Normalized Thermal Transient Impedance Curve

PACKAGE OUTLINE DIMENSIONS

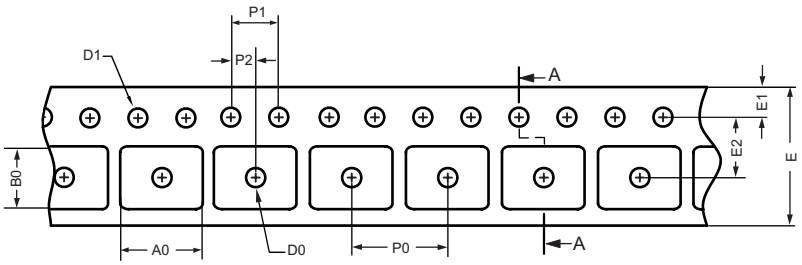
SO-8

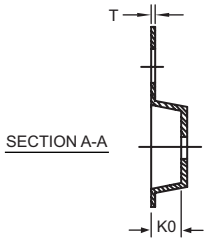


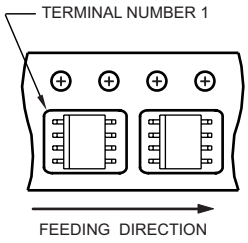
SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	1.63	0.049	0.064
b	0.31	0.51	0.012	0.020
C	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	3.70	4.00	0.146	0.157
e	1.27 REF.		0.050 BSC	
H	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°
h	0.25	0.50	0.010	0.020

SO-8 Tape and Reel Data

SO-8 Carrier Tape



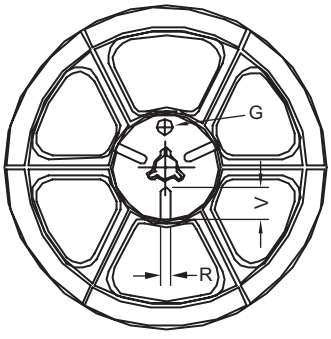


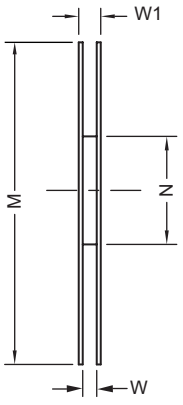


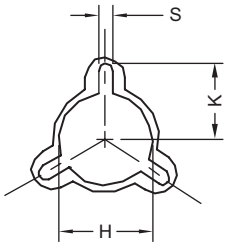
unit:㎜

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150㎜	6.50 ±0.15	5.25 ±0.10	2.10 ±0.10	ϕ1.5 (MIN)	ϕ1.55 ±0.10	12.0 +0.3 - 0.1	1.75 ±0.10	5.5 ±0.10	8.0 ±0.10	4.0 ±0.10	2.0 ±0.10	0.30 ±0.013

SO-8 Reel







UNIT:㎜

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 ㎜	ϕ330	330 ± 1	62 ±1.5	12.4 + 0.2	16.8 - 0.4	ϕ12.75 + 0.15	---	2.0 ±0.15	---	---	---